TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MH138FK

#### 3-to-8 Line Decoder

The TC7MH138FK is an advanced high speed CMOS 3-to-8 decoder fabricated with silicon gate  $\rm C^2MOS$  technology.

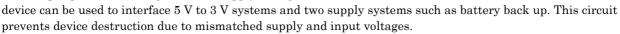
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

When the device is enabled, 3 binary select inputs (A, B and C) determine which one of the outputs  $(\overline{Y}0 - \overline{Y}7)$  will go low.

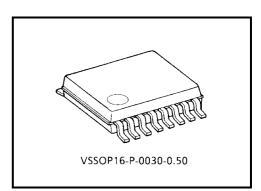
When enable input G1 is held low or either  $\overline{G}2A$  or  $\overline{G}2B$  is held high, decoding function is inhibited and all outputs go high.

G1,  $\overline{G}2A$ , and  $\overline{G}2B$  inputs are provided to ease cascade connection and for use as an address decoder for memory systems.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This



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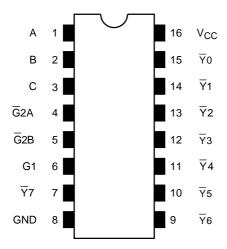


Weight: 0.02 g (typ.)

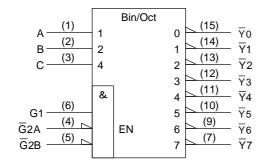
#### **Features**

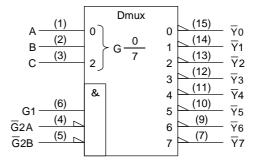
- High speed:  $t_{pd} = 5.7 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation:  $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays:  $t_pLH \approx t_pHL$
- Wide operating voltage range:  $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Pin and function compatible with 74ALS138

# Pin Assignment (top view)



# **IEC Logic Symbol**





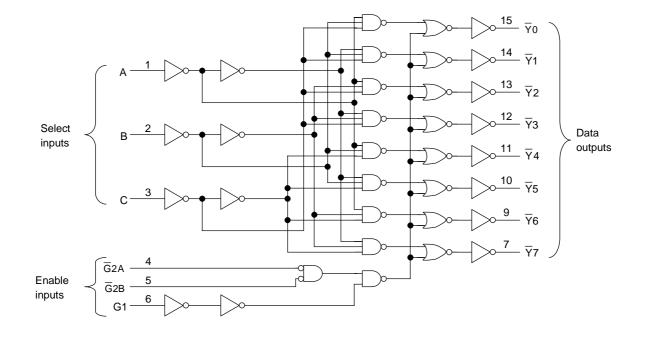
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# **Truth Table**

Inputs					Outputs									
	Enable		Select		<u></u>	<u></u>	<u></u>	_ Y3	<u>-</u> Y4	_ Y5	<u>-</u> Y6	<del>-</del> 77	Selected Output	
G1	G <sub>2</sub> A	G <sub>2</sub> B	C	В	Α	10	11	12	13	14	2	10	17	
L	Х	Х	Х	Х	Х	Н	Н	Н	Н	Н	Н	Н	Н	None
Х	Н	Х	Х	Х	Х	Н	Н	Н	Н	Н	Н	Н	Н	None
Х	Х	Н	Х	Х	Х	Н	Н	Н	Н	Н	Н	Н	Н	None
Н	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н	₹0
Н	L	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	₹1
Н	L	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н	Ÿ2
Н	L	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	<del>Y</del> 3
Н	L	L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Н	<del>Y</del> 4
Н	L	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н	<del>Y</del> 5
Н	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н	<del>-</del> 76
Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	<u>¥</u> 7

X: Don't care

# **Logic Diagram**



# **Maximum Ratings**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	٧
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	I <sub>OK</sub>	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±75	mA
Power dissipation	P <sub>D</sub>	180	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

# **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0~5.5	V
Input voltage	V <sub>IN</sub>	0~5.5	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	$0 \sim 100 \; (V_{CC} = 3.3 \pm 0.3 \; V)$	ns/V
Input noe and rail time	ui/uv	$0 \sim 20 \ (V_{CC} = 5 \pm 0.5 \ V)$	113/ V

# **Electrical Characteristics**

# **DC Characteristics**

Characte	Symbol	Test Condition			Ta = 25°C			Ta = -4	Unit		
Characte	HISTICS	Symbol	rest Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
			_		2.0	1.50	_	_	1.50	_	· V
Input voltage	High level	V <sub>IH</sub>			3.0~5.5	V <sub>CC</sub> × 0.7	_	_	V <sub>CC</sub> × 0.7	_	
input voitage					2.0			0.50	_	0.50	
	Low level	V <sub>IL</sub>		_	3.0~5.5			_ V <sub>CC</sub>			
		V <sub>ОН</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	2.0	1.9	2.0	_	1.9	_	
					3.0	2.9	3.0	_	2.9	_	
	High level				4.5	4.4	4.5	_	4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
Output voltage				$I_{OH} = -8 \text{ mA}$	4.5	3.94			3.80		V
Output voltage			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50 μA	2.0		0	0.1	_	0.1	
					3.0		0	0.1	_	0.1	
	Low level	V <sub>OL</sub>			4.5	_	0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36		0.44	
Input leakage cu	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0~5.5		_	±0.1	_	±1.0	μΑ	
Quiescent supply	Icc	$V_{IN} = V_{CC}$ or GND		5.5			4.0	_	40.0	μΑ	

# AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

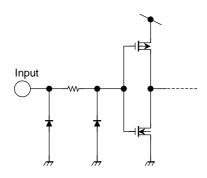
Characteristics	Symbol	Test Condition			-	Ta = 25°0		Ta = -4	Unit	
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Onit
			3.3 ± 0.3	15	_	8.2	11.4	1.0	13.5	- ns
Propagation delay time	t <sub>pLH</sub>			50	_	10.0	15.8	1.0	18.0	
(A, B, C- $\overline{Y}$ )	t <sub>pHL</sub>	_	5.0 ± 0.5	15	_	5.7	8.1	1.0	9.5	113
			5.0 ± 0.5	50		7.2	10.1	1.0	11.5	
	<sup>t</sup> pLH <sup>t</sup> pHL	_	3.3 ± 0.3	15	_	8.1	12.8	1.0	15.0	ns
Propagation delay time				50	_	10.6	16.3	1.0	18.5	
(G1- \overline{Y})			5.0 ± 0.5	15	_	5.6	8.1	1.0	9.5	
				50	_	7.1	10.1	1.0	11.5	
	<sup>t</sup> pLH <sup>t</sup> pHL	_	3.3 ± 0.3	15	_	8.2	11.4	1.0	13.5	
Propagation delay time				50	_	10.7	14.9	1.0	17.0	
( <del>G</del> 2 - <del>Y</del> )			5.0 ± 0.5	15	_	5.8	8.1	1.0	9.5	
				50	_	7.3	10.1	1.0	11.5	
Input capacitance	C <sub>IN</sub>	-			_	4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>			(Note)	_	34	_	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

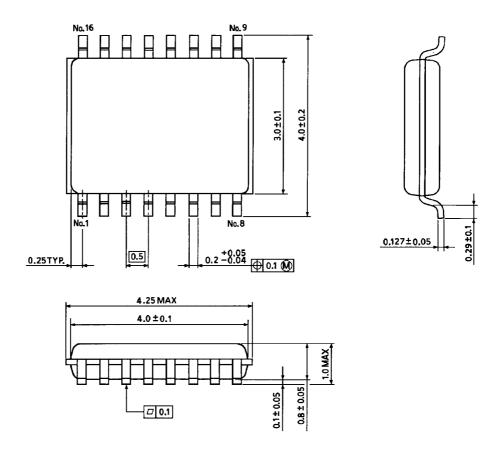
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

# **Input Equivalent Circuit**



# **Package Dimensions**



Weight: 0.02 g (typ.)

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